## ASSIGNMENT RECORDATION FORM COVER SHEET Patents Only

To: Commissioner for Patents:	Date: March 3, 2011 Attorney Docket No. 5649-3123
Please record the attached original documents or copy thereof.	Automey Docket No. 3049-3123
1. Name of conveying party(ies):	2. Name and address of receiving party(ies):
Hewlett-Packard Development Company, L.P. Hewlett-Packard Company	Samsung Electronics Co., Ltd.
,,,,,,,,,,,,,	416 Maetan-dong,
Additional name(s) of conveying party(ics) attached? Yes _x_ No	Yeongtong-gu, Suwon-si
3. Nature of conveyance:	Gyeonggi-do, Republic of Korea
x Assignment	\$ 55 · · / · · · · · · · · · · · · · · ·
Merger	
Security Agreement	
Change of Name Other	
Execution Date: [1.] April 21, 2010	
Execution Date: [1.] April 21, 2010	A 441421
	Additional name(s) & address(es) attached? Yes _x_ No
4. Application Patent Nos. Please See The Attached.  If this document is being filed together with a new application is:  Additional numbers attached? X Yes No	, the execution date of the application
5. Name and address of party to whom correspondence	6. Total number of applications and patents involved: 37
concerning document should be mailed:	7. Total fee (37 CFR 3.41) \$1480.00
Robert N. Crouse	Enclosed #1480.00
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Kirsten S. Carlos	

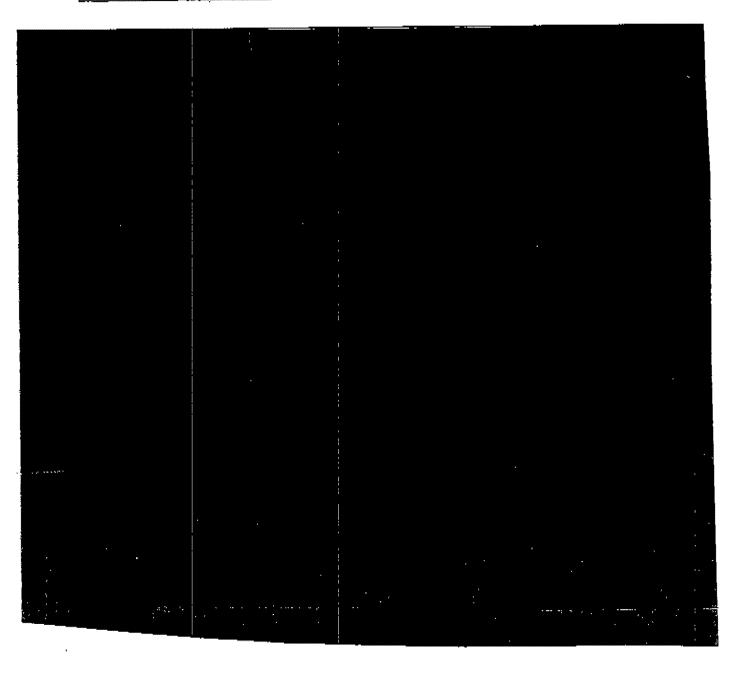
**PATENT** 

## Appendix A of Exhibit B: List of Assigned Patents

Tinital States Potents and Applications

US6643195 Self-healing MRAM US6829191 Magnetic memory equipped with a read control circuit and an output control circuit US6845896 Storage pack for use in high performance systems US6930370 Memory with conductors between or in communication with storage units US7290118 Address control system for a memory storage device US6898381 System and method for reading magnetization orientation of MRAM cells US7038941 Magnetic memory storage device US6898134 Systems and methods for sensing a memory element US6999366 Magnetic memory including a sense result category between logic states W6693275 Memory system having control circuit configured to receive data, provide encoded received data to match a fault pattern in the array of memory cells US683278 Memory device having memory cells capable of four states US6970799 Defective memory component of a memory device used to represent a data bit in a bit sequence US7103718 Non-volatile memory module for use in a computer system US6947333 Memory device US7167391 Multilayer pinned reference layer for a magnetic storage device US5835003 Colossal magnetoresistance sensor US5930087 Robust recording head for near-contact operation US7042783 Magnetic memory US721582 Method and system for controlling write current in magnetic memory US7215829 Method and system for controlling write current in magnetic memory US7193259 Top-pinned magnetoresistive device having adjusted interface property US7193259 Thermally written measietic memory device US7195927 Process for making magnetic memory storage device US7195927 Process for making magnetic memory structures having different-sized memory cell layers US710875 Hardmasks for providing thermally assisted switching of magnetic memory elements US7109917 Memory array method and system	United States Paten	United States Patents and Applications	
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U\$7149948	Manufacturing test for a fault tolerant magnetoresistive solid-state storage device
US20090047747	System and method for determining the value of a memory element
U\$6717234	Resistive Memory For Data Storage Devices
US6777270	Resistive Memory For Data Storage Devices
US6690597	MULTI-BIT PROM MEMORY CELL
US6567295	Addressing And Sensing A Cross-Point Diode Memory
US6385075	Parallel Access Of Cross-Point Diode Memory Arrays
US6552409	Fabrication Techniques For Addressing Cross-Point



## Exhibit B

## ASSIGNMENT OF PATENTS AND PATENT APPLICATIONS

WHEREAS, Hewlett-Packard Development Company, L.P., a limited partnership established and existing under the laws of the State of Texas and having its registered place of business at 20555 S.H. 249 Houston, Texas 77070, U.S.A. and Hewlett-Packard Company, a corporation organized and existing under the laws of the State of Delaware and having its principal place of business at 3000 Hanover Street, Palo Alto, California 94304, U.S.A. (collectively "HP") are the owners of record, either individually or collectively, of the Assigned Patents (as defined below);

WHEREAS, Samsung Electronics Co., Ltd. ("Samsung"), a corporation duly organized and existing under and by virtue of the laws of the Republic of Korea, and having a place of business at 416 Maetan-dong, Yeongtong-gu, Suwon-si, Gyeonggi-do, Republic of Korea, is desirous of acquiring the entire interest in and to the Assigned Patents (as defined below);

WHEREAS, HP and Samsung have entered into a Patent Purchase and Sale Agreement for certain patents and patent applications dated April 20, 2010 ("Purchase and Sale Agreement") wherein HP has agreed to sell and Samsung has agreed to purchase the Assigned Patents subject to all prior encumbrances and licenses;

WHEREAS, Samsung has agreed and covenanted in said Purchase and Sale Agreement to license back to HP certain rights under the Assigned Patents as a condition of and as part of the consideration for the Parties entering into the Purchase and Sale Agreement;

WHEREAS, for the purpose of this Assignment, the following terms, whether in singular or in plural form, when used with a capital initial letter shall have the respective meanings as follows.

"Affiliate" means with respect to any person, any other Person that directly, or indirectly through one or more intermediaries, controls, is controlled by, or is under the common control of the Person in question; provided, however, that in any country where the local law or regulation does not permit foreign equity participation of more than fifty percent (50%), an "Affiliate" shall include any Person in which the Person in question owns or controls, directly or indirectly, the maximum percentage of such outstanding stock or voting rights permitted by such local law or regulation. For purposes of the foregoing, "control," including the terms "controlling," "controlled by" and "under common control with," means the possession, direct or indirect, of the power to direct or cause the direction of the management and policies of a Person, whether through the ownership of voting securities, by contract or otherwise.

"Assigned Patents" means the issued patents and patent applications listed in Appendix A of this Assignment.

"Encumbrances" means any commitments, licenses or other rights relating to any of the Assigned Patents, whether express, implied or otherwise, that are made, entered into or granted by, or that arise from the actions taken by, HP, any current or former Affiliate of HP, or any Person, prior to the Effective Date including, but not limited to, the commitments, licenses and rights described in Sections 5 and 6.1 of the Purchase and Sale Agreement.

"Person" means any natural person, corporation, company, partnership, association, sole proprietorship, trust, joint venture, non-profit entity, institute, governmental authority, trust association or other form of entity not specifically listed herein including, without limitation, HP or any of its Affiliates, or Samsung or any of its Affiliates.

NOW, THEREFORE, to all whom it may concern, be it known that for good and valuable consideration to HP in hand paid, the receipt of which is hereby acknowledged, HP has sold, assigned, transferred, and set over, and by these presents does sell, assign, transfer, and set over unto said Samsung, subject to all Encumbrances, its whole right, title, and interest in and to all of the Assigned Patents, said whole right, title, and interest in and to said Assigned Patents including all past, present, and future causes of action and claims for damages derived by reason of patent infringement thereof (to the extent such damages are not already paid, awarded or contractually owed to HP, its Affiliates or any predecessor of HP or HP's Affiliates), for said Samsung's own use and for the use of its assigns, successors, and legal representatives to the full end of the term of each of the Assigned Patents. For clarity, the foregoing assignment does not include (i) any trademarks, trade dress, trade names, or other indicia of origin; (ii) except for inventions of the Assigned Patents, any inventions or discoveries, whether patentable or not, and registrations, invention disclosures, patents and applications therefor; (iii) any trade secrets, confidential information or know-how; (iv) any works of authorship, whether copyrightable or not; and (v) any other intellectual property or proprietary rights of HP, its Affiliates or any predecessor of HP or HP's Affiliates.

HP, for itself, and its heirs, assigns, and legal representatives hereby further covenants to and with Samsung, its assigns, successors, and legal representatives to fully cooperate therewith in perfecting this assignment in the United States and in any and all foreign jurisdictions, said cooperation extending to the Assigned Patents, and including the execution of additional assignments or other formal documents as may be required in connection therewith.

In Testimony Whereof, HP by its fully authorized representatives has executed this Assignment as of the dates indicated below.

4/21/10

Date:

HEWLETT-PACKARD DEVELOPMENT COMPANY, L.P.

By: HPO/Holdings/LIC/its/General Partner

Paul T. Porrini Kevin P. Light, Manager HPQ Holdings, LLC

By:

Bruce H. Watrous, Jr.
VP & AGC, Intellectual Property Licensing

Hewlett-Packard Company